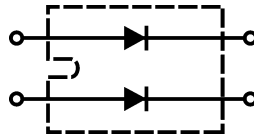


Fast Recovery Epitaxial Diode (FRED)

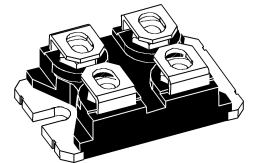
DSEI 2x 121

$I_{FAVM} = 2 \times 123 \text{ A}$
 $V_{RRM} = 200 \text{ V}$
 $t_{rr} = 35 \text{ ns}$

V_{RSM} V	V_{RRM} V	Type
200	200	DSEI 2x 121-02A



miniBLOC, SOT-227 B
 E72873



Symbol	Test Conditions	Maximum Ratings (per diode)	
I_{FRMS} I_{FAVM} ① I_{FRM}	$T_{VJ} = T_{VJM}$ $T_C = 70^\circ\text{C}$; rectangular, $d = 0.5$ $t_p < 10 \mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	150 123 600	A A A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1200 1300	A A
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1080 1170	A A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	7200 7100	A^2s A^2s
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	5800 5700	A^2s A^2s
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-40...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	250	W
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
M_d	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

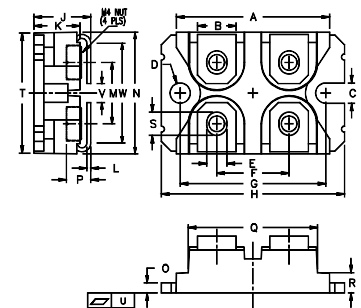
Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$		1 0.5 20 mA mA mA
V_F	$I_F = 120 \text{ A}$; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	0.89	0.95 1.10 V V
V_{T0}	For power-loss calculations only		0.7 V
r_T	$T_{VJ} = T_{VJM}$		2.1 $\text{m}\Omega$
R_{thJC} R_{thCK}		0.1	0.5 K/W K/W
t_{rr}	$I_F = 1 \text{ A}$; $-di/dt = 400 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	35	50 ns
I_{RM}	$V_R = 100 \text{ V}$; $I_F = 100 \text{ A}$; $-di_F/dt = 200 \text{ A}/\mu\text{s}$ $L \leq 0.05 \mu\text{H}$; $T_{VJ} = 100^\circ\text{C}$	12	15 A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $d = 0.5$
 Data according to IEC 60747
 IXYS reserves the right to change limits, test conditions and dimensions

Features

- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 2500 V~
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

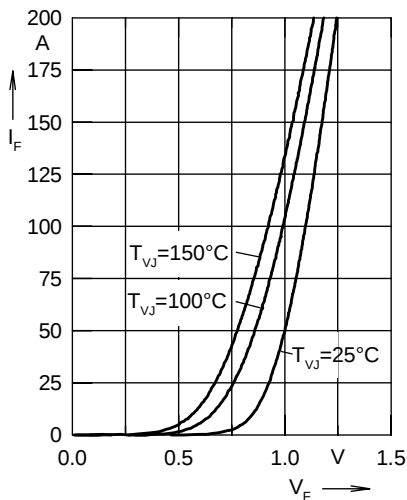


Fig. 1 Forward current I_F versus V_F

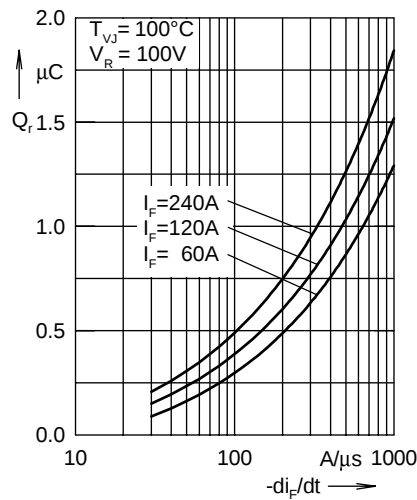


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

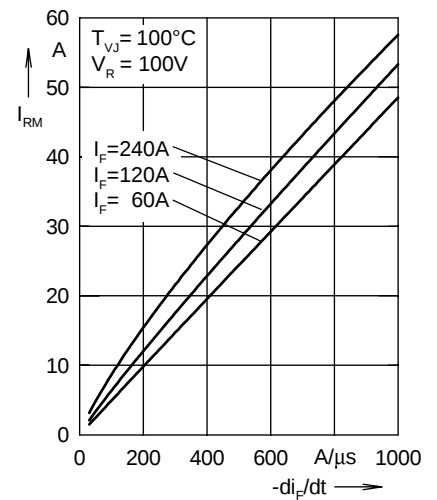


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

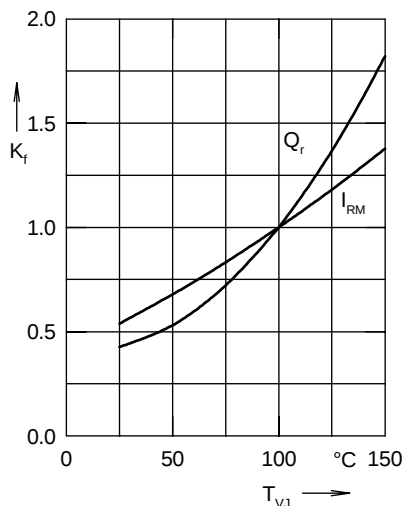


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

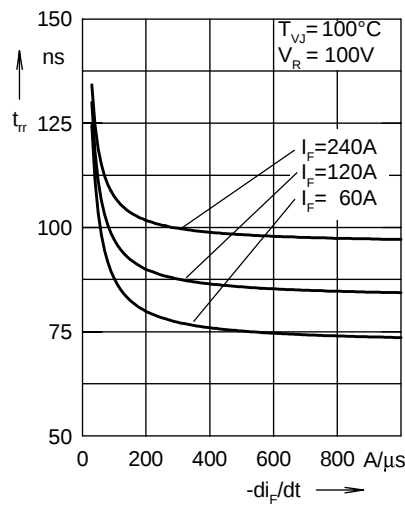


Fig. 5 Typ. recovery time t_{tr} versus $-di_F/dt$

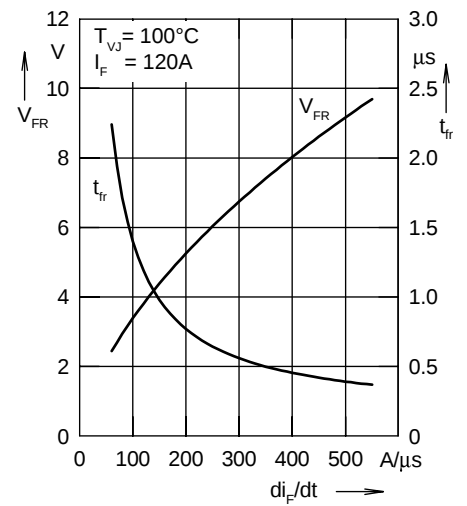


Fig. 6 Typ. peak forward voltage V_{FR} and t_{tr} versus di_F/dt

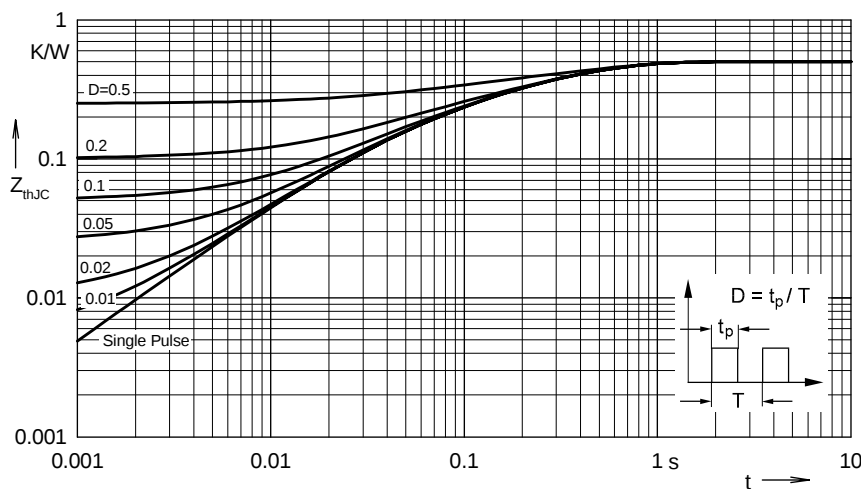


Fig. 7 Transient thermal impedance junction to case at various duty cycles

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0725	0.028
2	0.1423	0.092
3	0.2852	0.35